

General Description

The MY50N06P uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

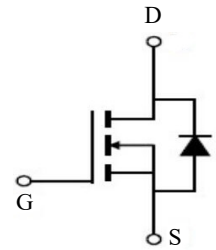
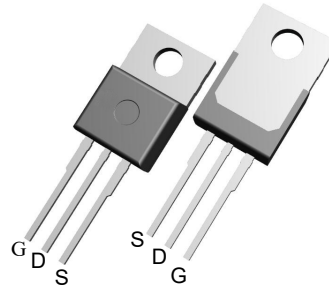


Features

V_{DSS}	60	V
I_D	50	A
$R_{DS(ON)}(at V_{GS}=10V)$	15	$m\Omega$
$R_{DS(ON)}(at V_{GS}=4.5V)$	16	$m\Omega$

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY50N06P	TO-220	MY50N06P	1000

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_c=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D@T_c=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	25	A
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.4	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	6	A
I_{DM}	Pulsed Drain Current ²	90	A
EAS	Single Pulse Avalanche Energy ³	39.2	mJ
I_{AS}	Avalanche Current	28	A
$P_D@T_c=25^\circ\text{C}$	Total Power Dissipation ⁴	45	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.063	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=15A$	---	15	19	$m\Omega$
		$V_{GS}=4.5V$, $I_D=10A$	---	16	25	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.24	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=48V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=15A$	---	17	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	3.2	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=48V$, $V_{GS}=4.5V$, $I_D=12A$	---	12.6	---	nC
Q_{gs}	Gate-Source Charge		---	3.2	---	
Q_{gd}	Gate-Drain Charge		---	6.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V$, $V_{GS}=10V$, $R_G=3.3\Omega$, $I_D=10A$	---	8	---	ns
T_r	Rise Time		---	14.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24.4	---	
T_f	Fall Time		---	4.6	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1MHz$	---	1500	---	pF
C_{oss}	Output Capacitance		---	132	---	
C_{rss}	Reverse Transfer Capacitance		---	88	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	23	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	46	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=22.6A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

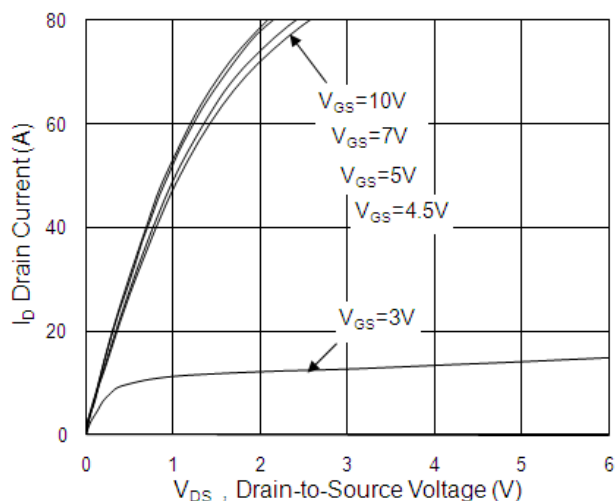


Fig.1 Typical Output Characteristics

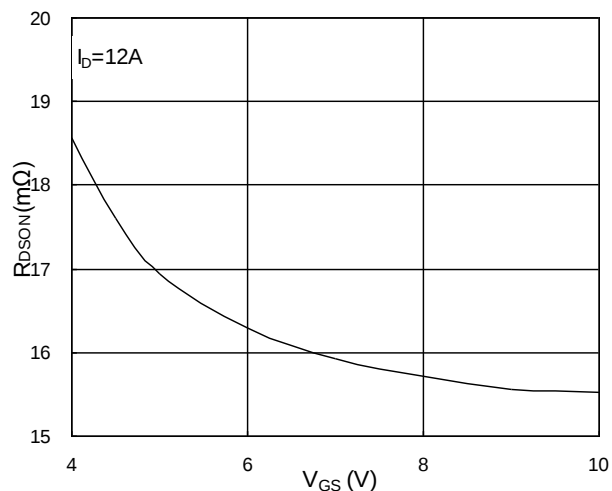


Fig.2 On-Resistance v.s Gate-Source

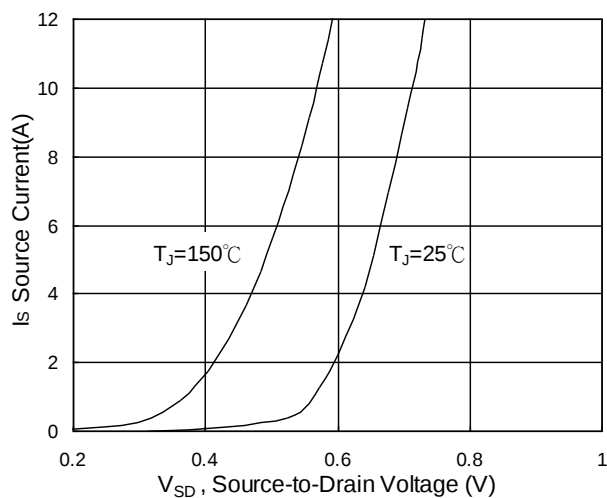


Fig.3 Forward Characteristics of Reverse

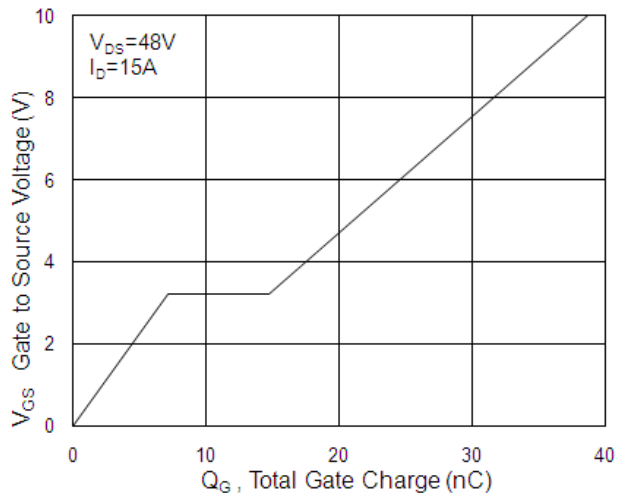


Fig.4 Gate-Charge Characteristics

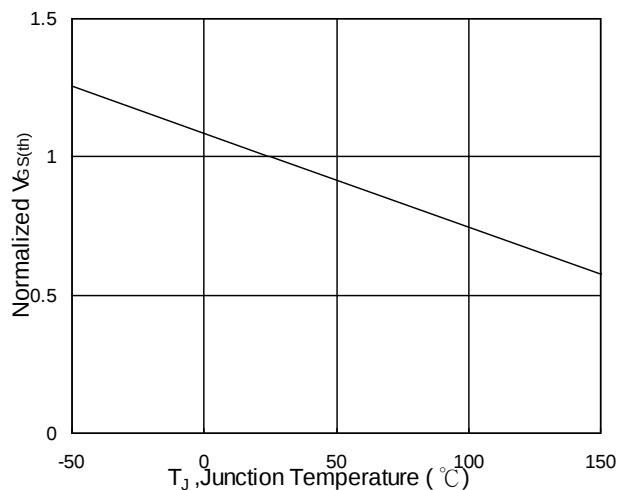


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

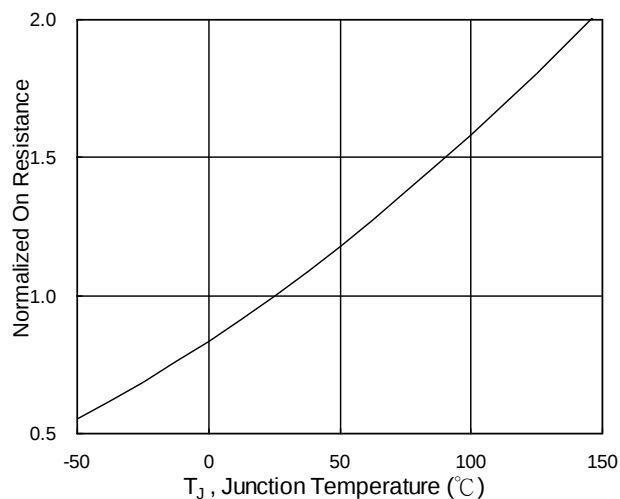


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

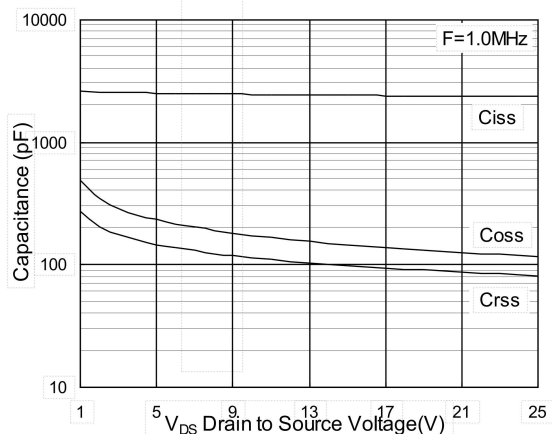


Fig.7 Capacitance

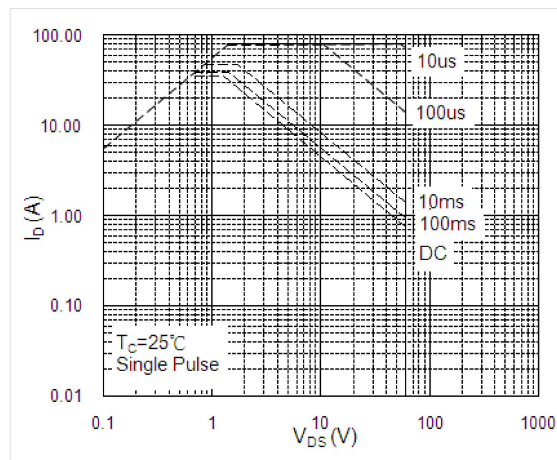


Fig.8 Safe Operating Area

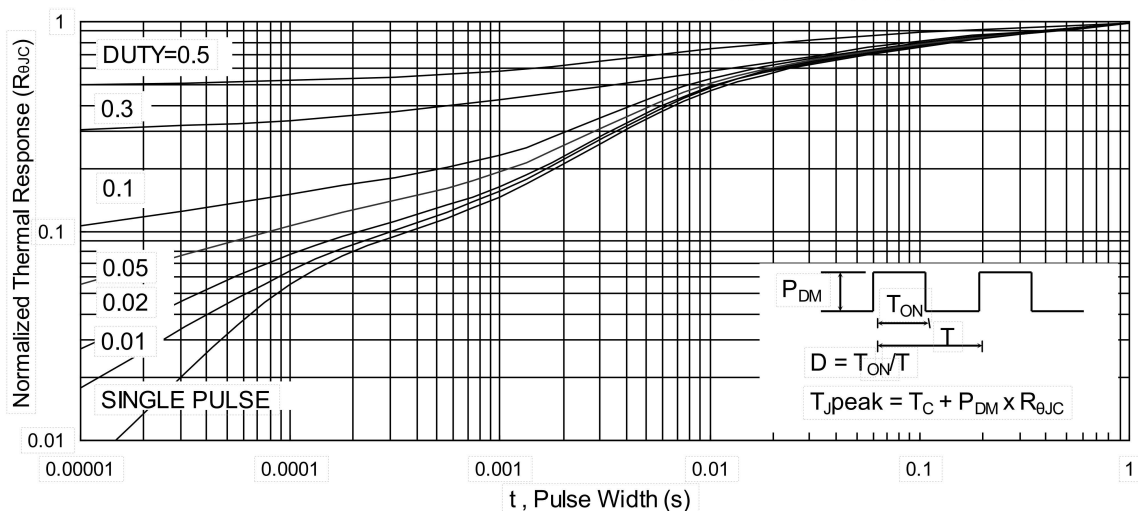


Fig.9 Normalized Maximum Transient Thermal Impedance

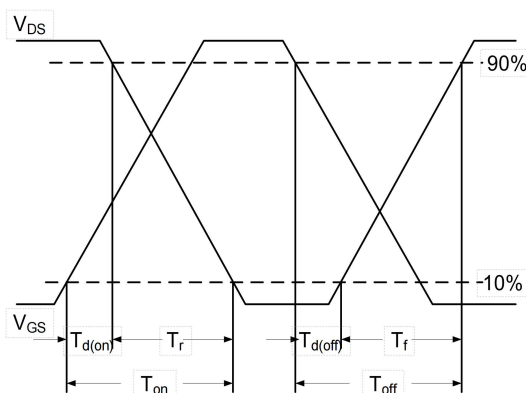


Fig.10 Switching Time Waveform

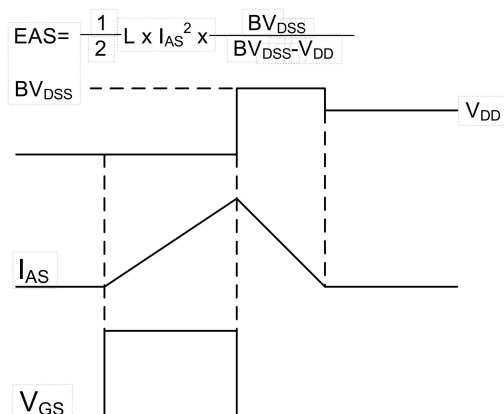


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-TO-220-JQ Single

